

Product Overview

MBR360: Schottky Barrier Rectifier, 60 V, 3.0 A

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. The Schottky Rectifier's state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. It is ideally suited for use as rectifiers in low voltage, high frequency inverters, free wheeling diodes and polarity protection diodes.

Features

- Extremely Low v_F
 - Low Power Loss/High Efficiency
 - Highly Stable Oxide Passivated Junction
 - Low Stored Charge, Majority Carrier Conduction
 - Case: Epoxy, Molded
 - Weight: 1.1 gram (approximately)
 - Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
 - Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
 - Shipped in plastic bags, 5,000 per bag
 - Available Tape and Reeled, 1500 per reel, by adding a "RL" suffix to the part number
- For more features, see the data sheet

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (μ A)	$I_{O(max)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C_j Max (pF)	Package Type
MBR360G	0.1141	Pb-free	Active	Single	60	0.74	600	3	80	-	-	Axial Lead-2
		Halide free										
MBR360RLG	0.1109	Pb-free Halide free	Active	Single	60	0.74	600	3	80	-	-	Axial Lead-2

For more information please contact your local sales support at www.onsemi.com.

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